

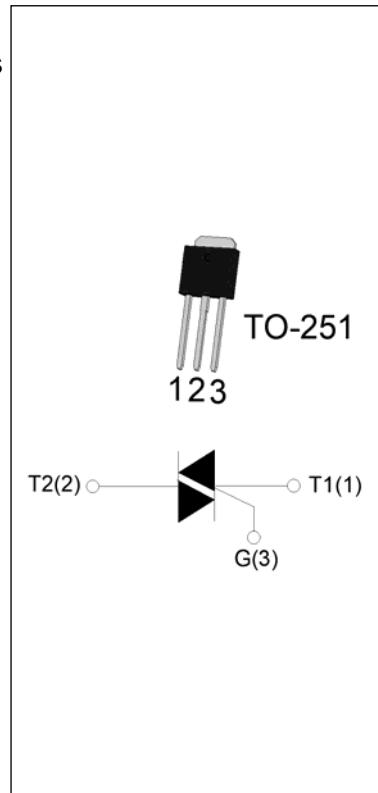


T0810H-6H 8A TRIAC

Rev.A.1.0

DESCRIPTION:

The T0810H-6H triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T0810H-6H provides a very high switching capability up to junction temperatures of 150°C. It can be driven directly through the MCU I/O port. From T2 terminals to external heatsink. Package TO-251 is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\text{ I/II/III}}$	10/10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-150	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_c \leq 119^\circ\text{C}$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		88	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=150^\circ\text{C}$)	di/dt	50	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=150^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150^\circ\text{C}$)	$P_{G(AV)}$	1	W

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	I - II - III	MAX.	10	mA
V_{GT}		I - II - III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150^\circ C$ $R_L=3.3K\Omega$	I - II - III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	25	mA
		II		40	
I_H	$I_T=100mA$		MAX.	25	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150^\circ C$		MIN.	200	V/ μs
$(dI/dt)c$	$(dV/dt)c=20V/\mu s$, $T_j=150^\circ C$		MIN.	1.8	A/ms
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25^\circ C$	TYP.	2.5	μs	
t_{off}			25		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=11A$	$t_p=380\mu s$	$T_j=25^\circ C$	1.4
V_{TO}	Threshold voltage		$T_j=150^\circ C$	0.78
R_D	Dynamic resistance		$T_j=150^\circ C$	$m\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=150^\circ C$	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	3	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (AC)	100	$^\circ C/W$

ORDERING INFORMATION

T	08	10	H	-6	H
Triacs					H:TO-251
	<u>$I_T(\text{RMS})=8A$</u>				<u>$6: V_{\text{DRM}} / V_{\text{RRM}} \geq 600V$</u>
		<u>$10: I_{GT1-3} \leq 10mA$</u>			High junction temperature

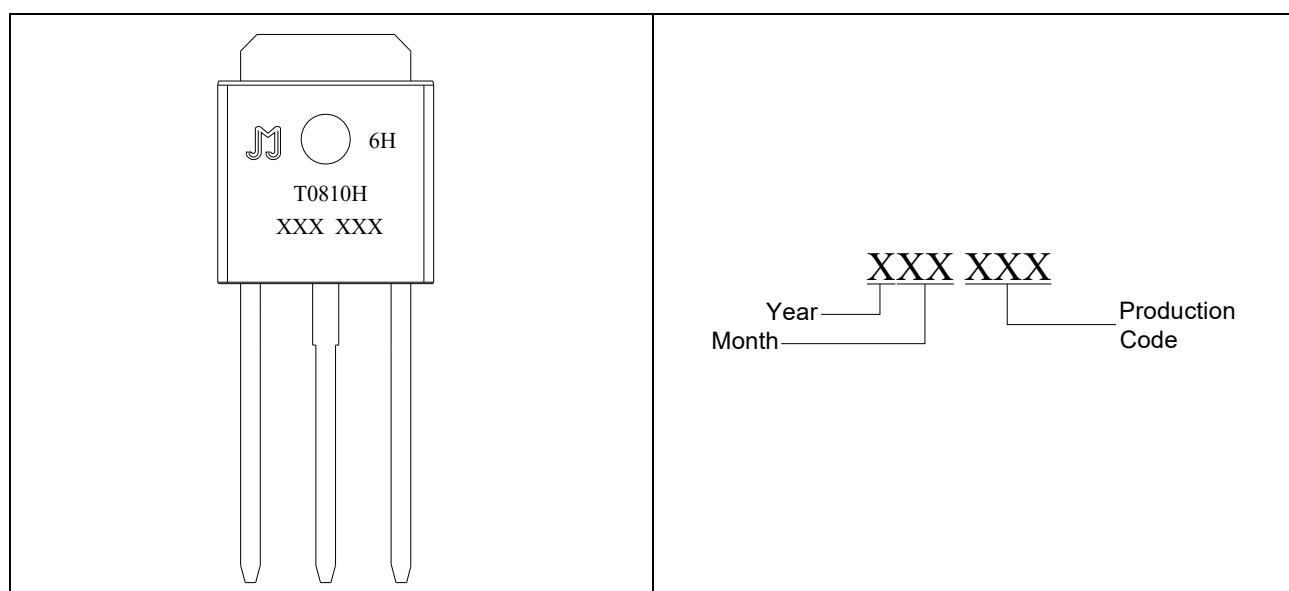
MARKING

FIG.1 Maximum power dissipation versus RMS on-state current

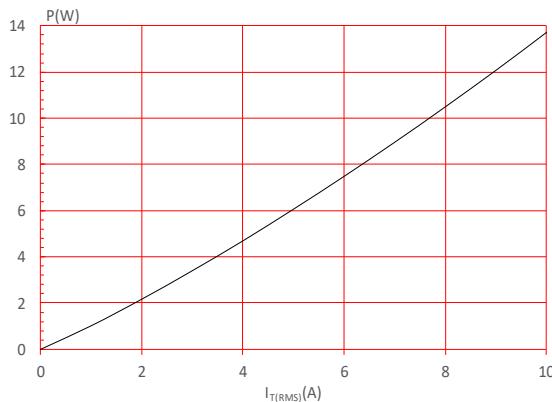


FIG.3: Surge peak on-state current versus number of cycles

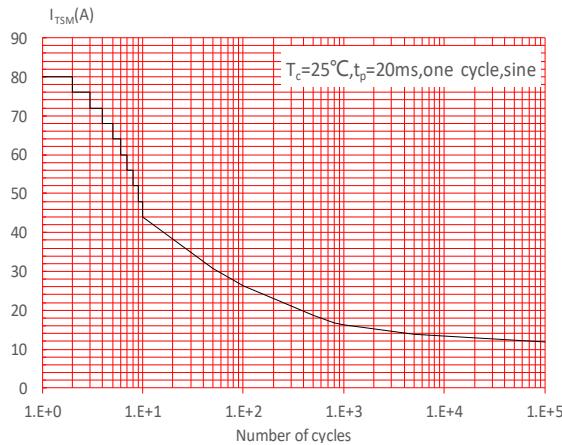


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dI/dt < 50\text{A}/\mu\text{s}$)

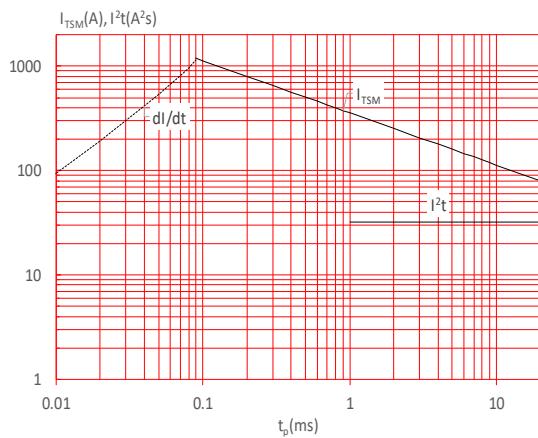


FIG.2: RMS on-state current versus case temperature

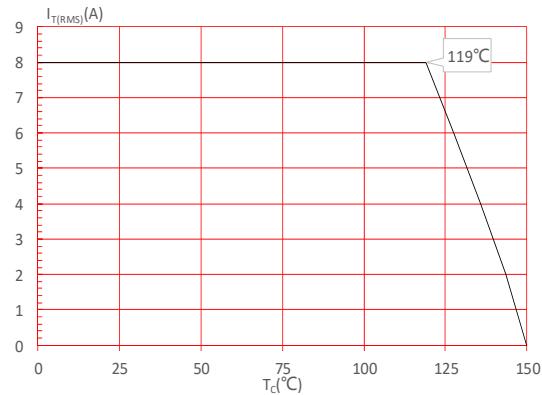


FIG.4: On-state characteristics

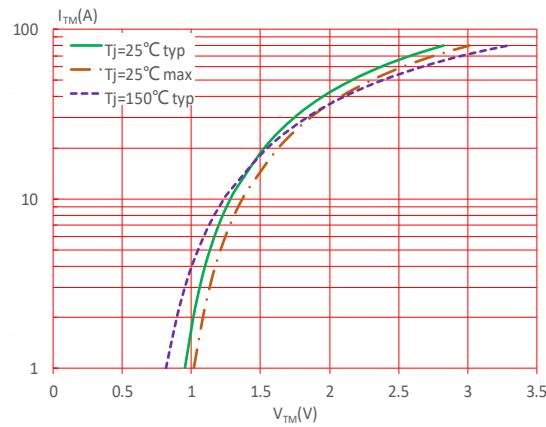


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

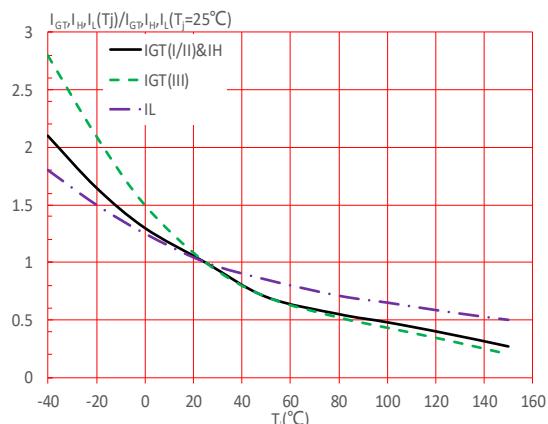
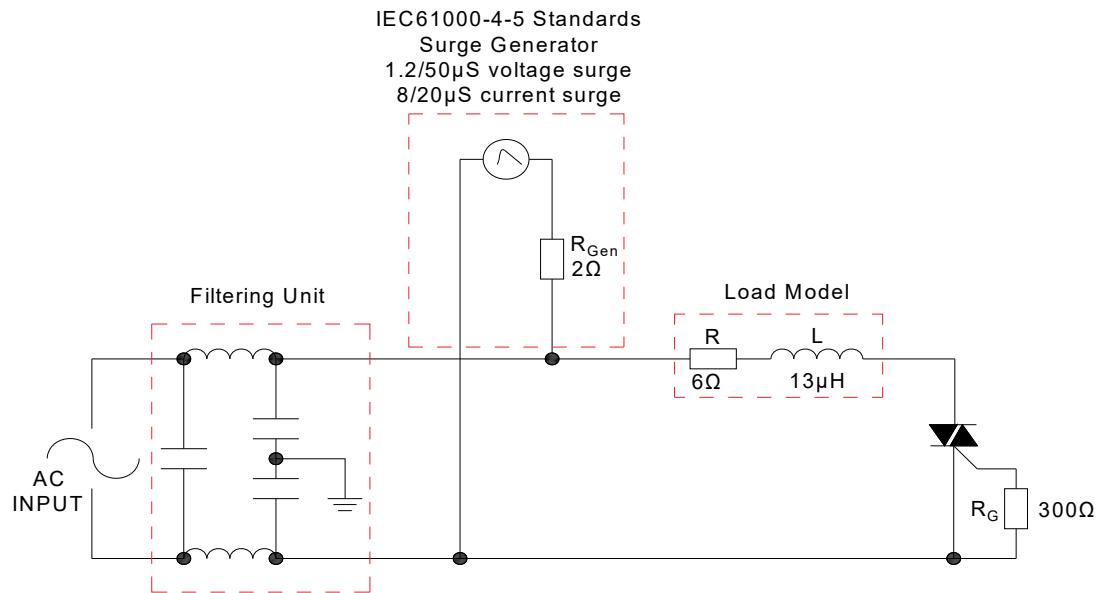


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

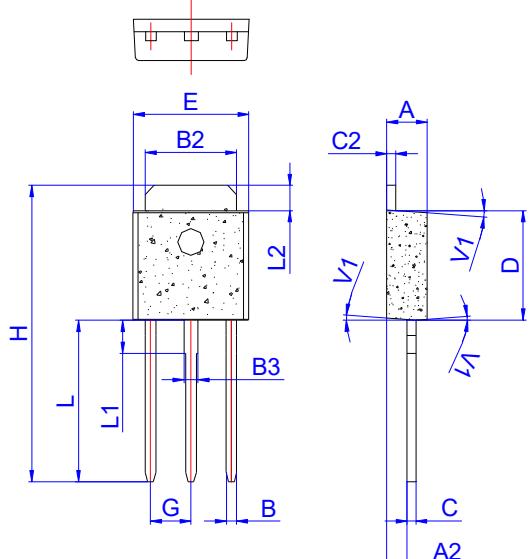
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I -II-III			
T0810H-6H	600	10	TO-251	80	Tube

Document Revision History

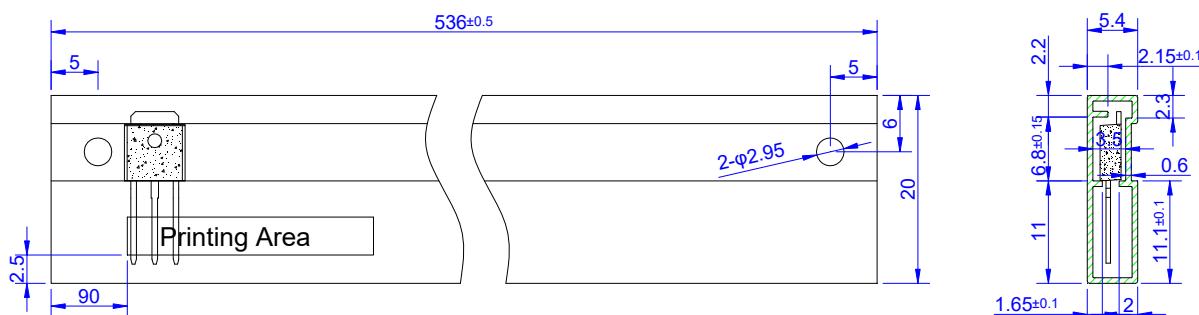
Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	2.20		2.40	0.087		0.094
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		2.20	0.071		0.087
L2	1.25		1.55	0.049		0.061
V1			4°			4°

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-251	TUBE	80	4,000	20,000

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